

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	substrate and "amorphous silicon layer" and optic\$4 and pattern\$4 and mask and hitch and sink and laser and anneal\$4 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 08:46
L2	0	substrate and "amorphous silicon" and optic\$4 and pattern\$4 and mask and hitch and sink and laser and anneal\$4 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 08:46
L3	85	substrate and "amorphous silicon" and optic\$4 and pattern\$4 and mask and sink and laser and anneal\$4 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 09:33
L4	5	substrate and "amorphous silicon" and optic\$4 and pattern\$4 and mask and sink and laser and anneal\$4 and polysilicon and (anti-reflective)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 08:58
L5	1	"polysilicon film" and substrate and "amorphous silicon" and optic\$4 and pattern and mask and etch\$4 and "heat sink" and "anti-reflective" and laser and anneal\$4 and molten and channel and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 09:05
L6	1	"polysilicon film" and substrate and "amorphous silicon" and optic\$4 and pattern and mask and etch\$4 and "heat sink" and "anti-reflective" and laser and anneal\$4 and crystalliz\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 09:05
L7	1	"polysilicon film" and substrate and "amorphous silicon" and optic\$4 and pattern and mask and etch\$4 and "heat sink" and "anti-reflective" and laser and anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 09:06
L8	1	"polysilicon film" and substrate and "amorphous silicon" and optic\$4 and pattern and mask and etch\$4 and "heat sink" and "anti-reflective"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 09:06
L9	2	polysilicon and substrate and "amorphous silicon" and optic\$4 and pattern and mask and etch\$4 and "heat sink" and "anti-reflective"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/03 09:06

S1	0	substrate and "amorphous silicon" and "optical layer" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:34
S2	73	substrate and "amorphous silicon" and optical and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:35
S3	2	substrate and "amorphous silicon" and optical and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and pattern\$8 and mask and (anisotropic near4 etch) and (silicon near4 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:48
S4	94	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:49
S5	54	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:49
S6	24	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:50
S7	0	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask) and "anisotropic etch"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:51
S8	7	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask) and "anisotropic"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:52

S9	6	substrate and "amorphous silicon" and optical and "silicon nitride" and reflect\$8 and (laser near4 anneal\$4) and molten and crystal\$8 and polysilicon and (pattern near4 mask) and "anisotropic" and "silicon oxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/16 12:52
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